

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
650V	0.37Ω@10V	18A

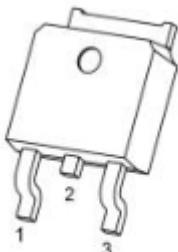
## Feature

- Fast Switching
- Improved dv/dt capability
- 100% Single Pulse avalanche energy Test

## Applications

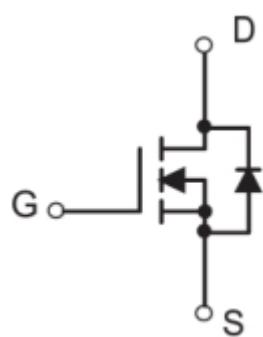
- DC Motor Control and Class D Amplifier
- Uninterruptible Power Supply (UPS)

## Package

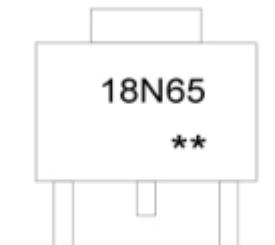


TO-252-2L(G:1 D:2 S:3)

## Circuit diagram



## Marking



18N65 : Product code  
 \*\* : Week code.

## Absolute maximum ratings

( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current( $T_C = 25^\circ\text{C}$ )	$I_D$	18	W
Pulsed Drain Current	$I_{DM}$	72	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	500	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	65	W
Thermal Resistance Junction- Case <sup>1</sup>	$R_{\Theta JC}$	1.92	$^\circ\text{C} / \text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG},$	-55~ +150	$^\circ\text{C}$

## Electrical characteristics

( $T_A=25^\circ\text{C}$ , unless otherwise noted)

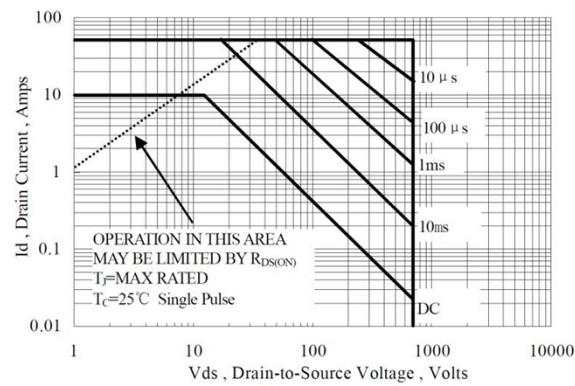
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	650			V
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = 650\text{V}, V_{\text{GS}} = 0\text{V}, T_j = 25^\circ\text{C}$			1	$\mu\text{A}$
Gate-body leakage current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 30\text{V}, V_{\text{DS}} = 0\text{V}$			$\pm 100$	$\mu\text{A}$
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	2		4	V
Static Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 5\text{A}$		0.37	0.46	$\Omega$
<b>Dynamic characteristics<sup>4</sup></b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		2442		pF
Output Capacitance	$C_{\text{oss}}$			190		
Reverse Transfer Capacitance	$C_{\text{rss}}$			14		
Total Gate Charge(4.5V)	$Q_g$	$V_{\text{DS}} = 520\text{V}, I_{\text{D}} = 18\text{A}, V_{\text{GS}} = 10\text{V}$		42		nC
Gate-Source Charge	$Q_{\text{gs}}$			12		
Gate-Drain Charge	$Q_{\text{gd}}$			16.3		
<b>Switching Characteristics</b>						
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DS}} = 15\text{V}, I_{\text{D}} = 10\text{A}, R_{\text{GEN}} = 1.8\Omega, V_{\text{GS}} = 4.5\text{V}$		11		nS
Rise Time	$T_r$			120		
Turn-Off Delay Time	$T_{\text{d(off)}}$			25		
Fall Time	$T_f$			60		
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Maximum Continuous Drain to Source Diode Forward Current	$I_s$				130	A
Maximum Pulsed Drain to Source Diode Forward Current	$I_{\text{SM}}$				360	A
Drain to Source Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}} = 0\text{V}, I_s = 20\text{A}$			1.2	V
Body Diode Reverse Recovery Time	$t_{\text{rr}}$	$I_F = 60\text{A}, dI/dt = 100\text{A}/\mu\text{s}$		56		ns
Body Diode Reverse Recovery Time Charge	$Q_{\text{rr}}$			110		nC

### Note :

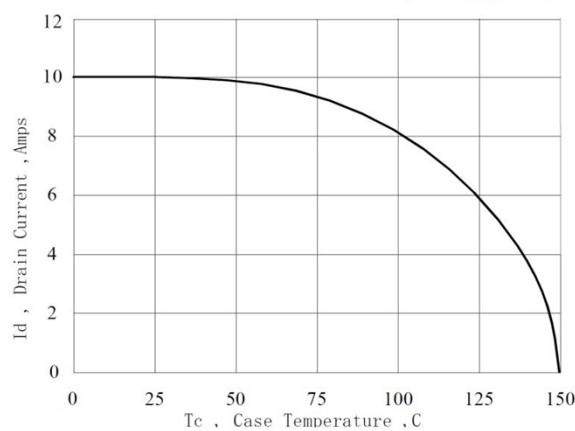
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_j = 25^\circ\text{C}, V_G = 10\text{V}, L = 30\text{mH}, R_g = 25\Omega, V_{\text{DD}} = 100\text{V}$

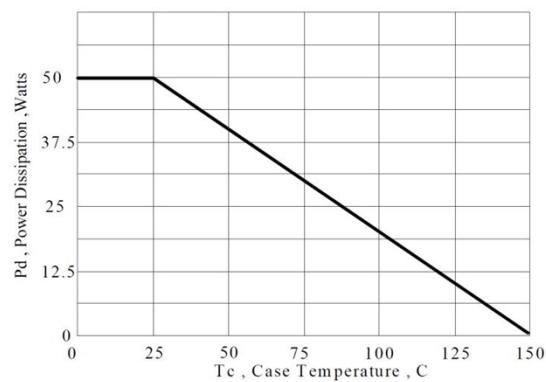
## Typical Characteristics



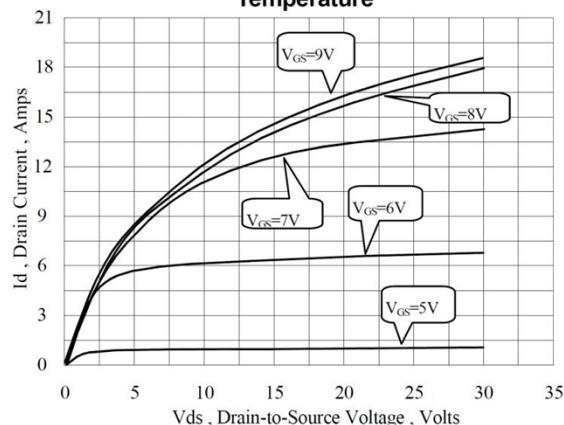
**Maximum Forward Bias Safe Operating Area**



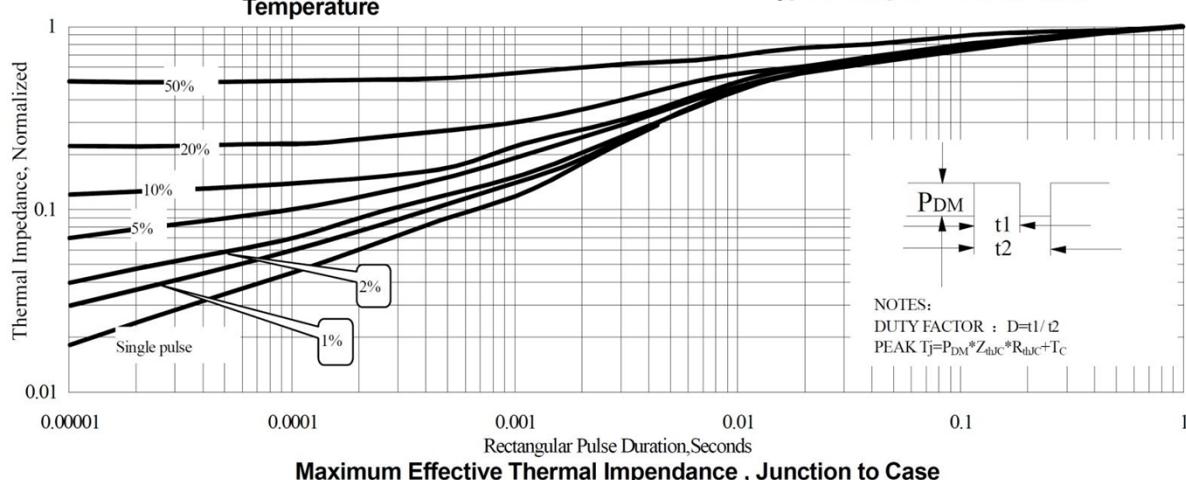
**Maximum Continuous Drain Current vs Case Temperature**



**Maximum Power Dissipation vs Case Temperature**



**Typical Output Characteristics**



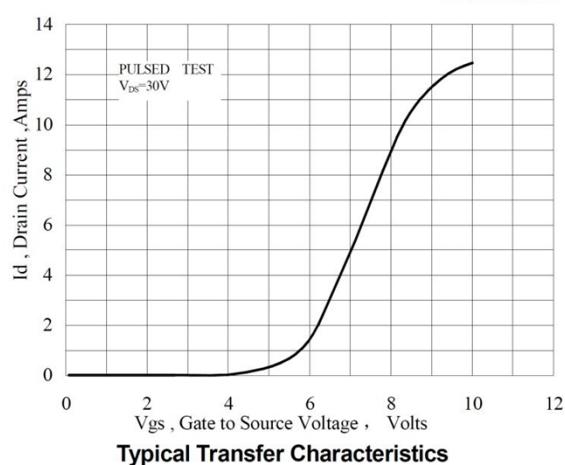
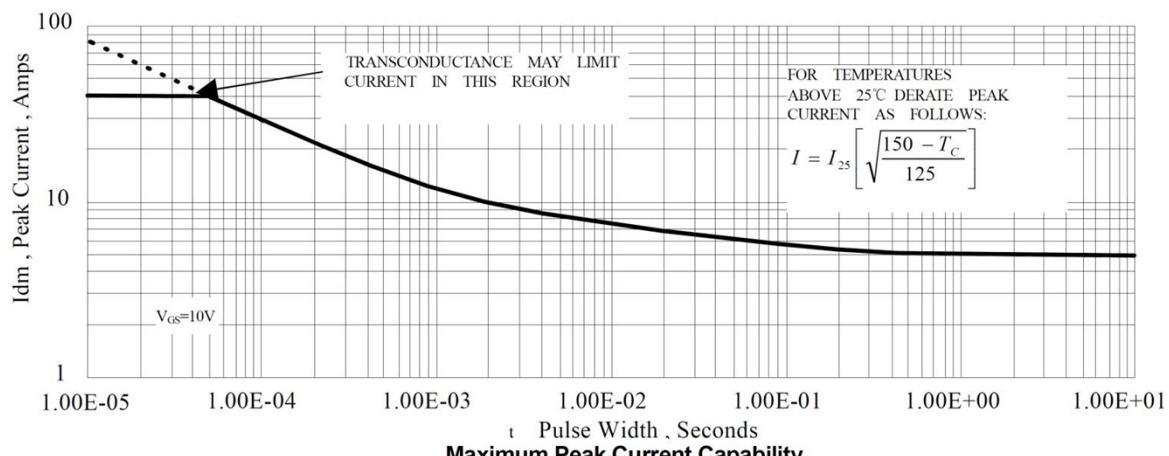
NOTES:  
 DUTY FACTOR :  $D=t_1/t_2$   
 PEAK  $T_j=P_{DM} \cdot Z_{JJC} \cdot R_{dJJC} + T_c$

**Maximum Effective Thermal Impedance , Junction to Case**

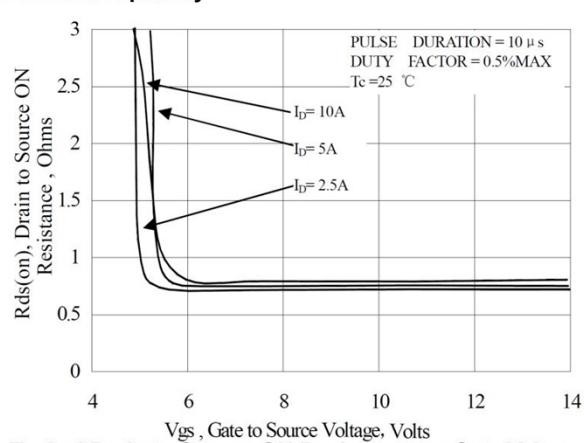


ZL MOSFET

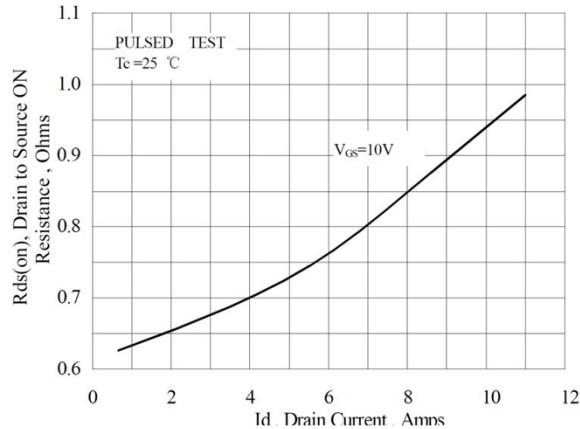
ZL18N65



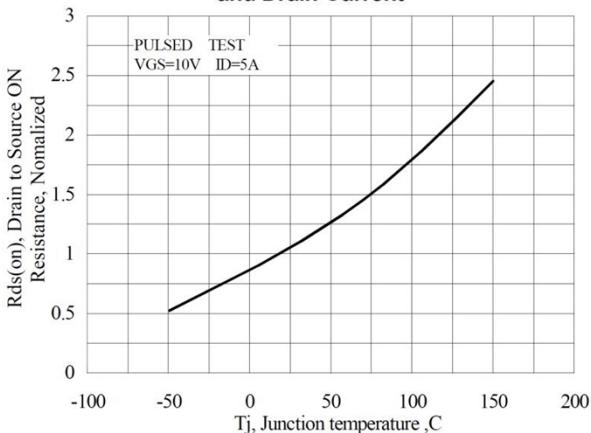
Typical Transfer Characteristics



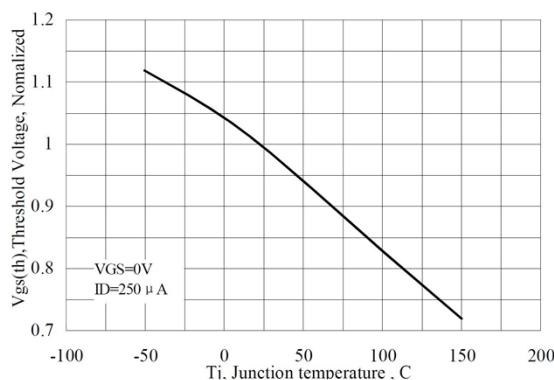
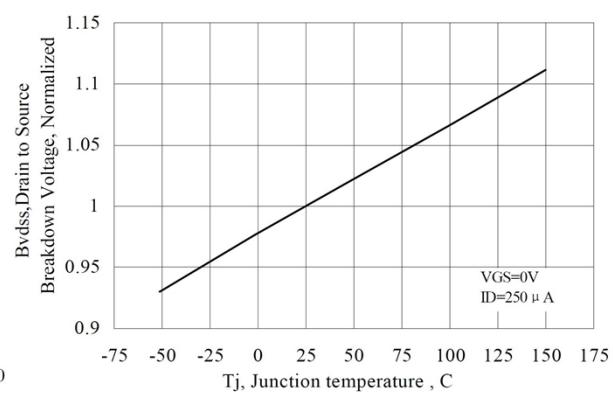
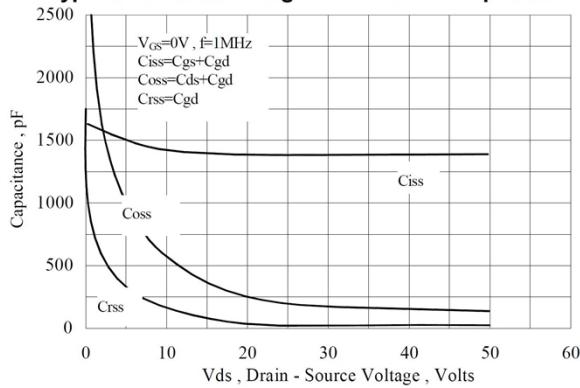
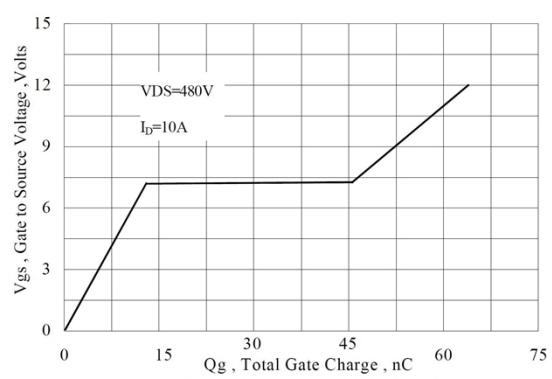
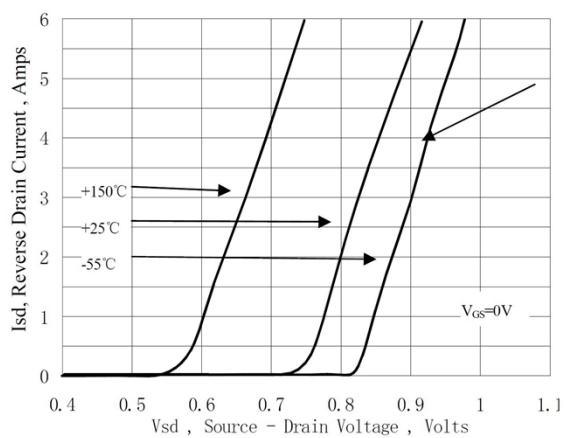
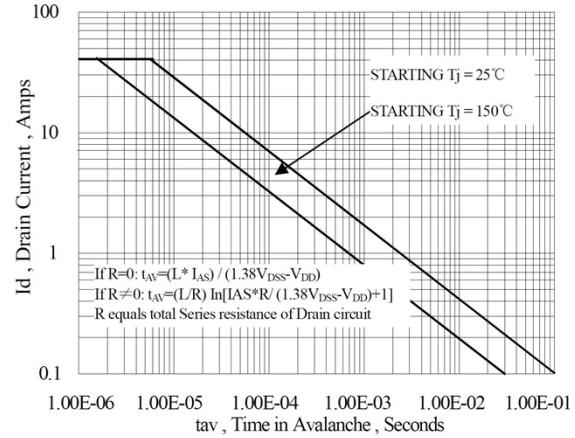
Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current



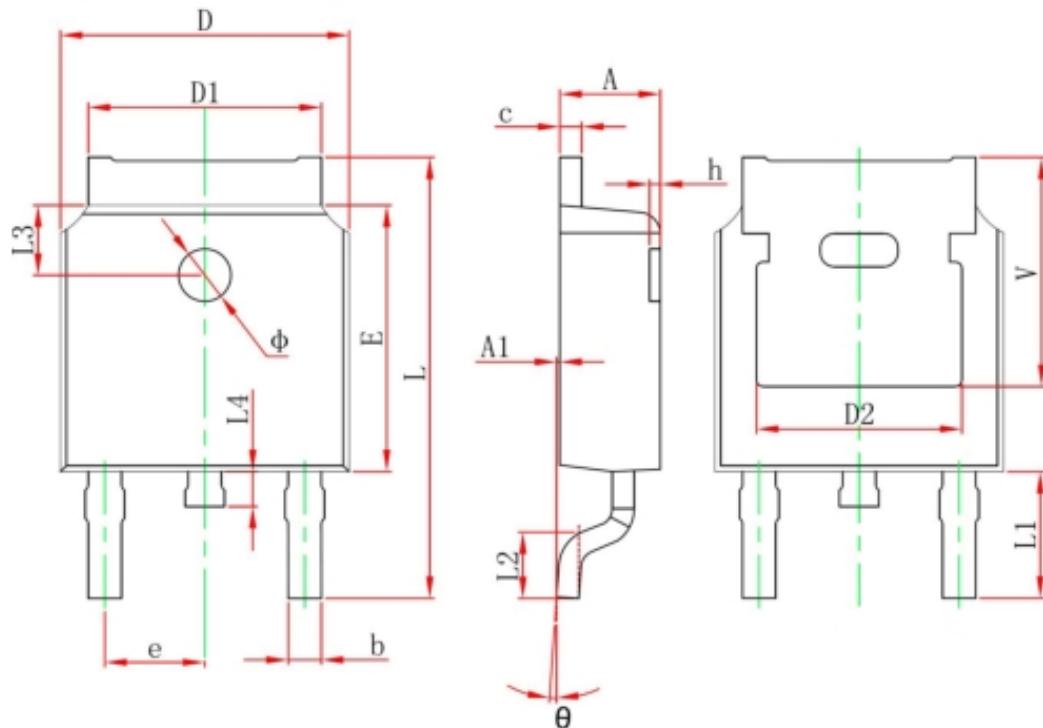
Typical Drain to Source ON Resistance vs Drain Current



Typical Drain to Source on Resistance vs Junction Temperature


**Typical Threshold Voltage vs Junction Temperature**

**Typical Breakdown Voltage vs Junction Temperature**

**Typical Capacitance vs Drain to Source Voltage**

**Typical Gate Charge vs Gate to Source Voltage**

**Typical Body Diode Transfer Characteristics**

**Maximum Forward Bias Safe Operating Area**

## TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	